

25Gb/s Photodiode Chip

CPL2520S

Features

- InGaAs/InP PIN-PD with integrated backside lens
- Coplanar GSG contact pads
- Low cost and High reliability

Applications

- Receiver for 100GbE and OTU4
- Datacom and Telecom up to 28Gb/s

Absolute Maximum Ratings

Parameters	Symbol	Rating	Unit
Reverse voltage	V_R	20	V
Reverse current	I_R	2	mA
Forward current	I_F	10	mA
Optical input power	P_{max}	5	dBm
Operating temperature range	T_C	-40 to +85	°C
Storage temperature range	T_{STG}	-40 to +125	°C

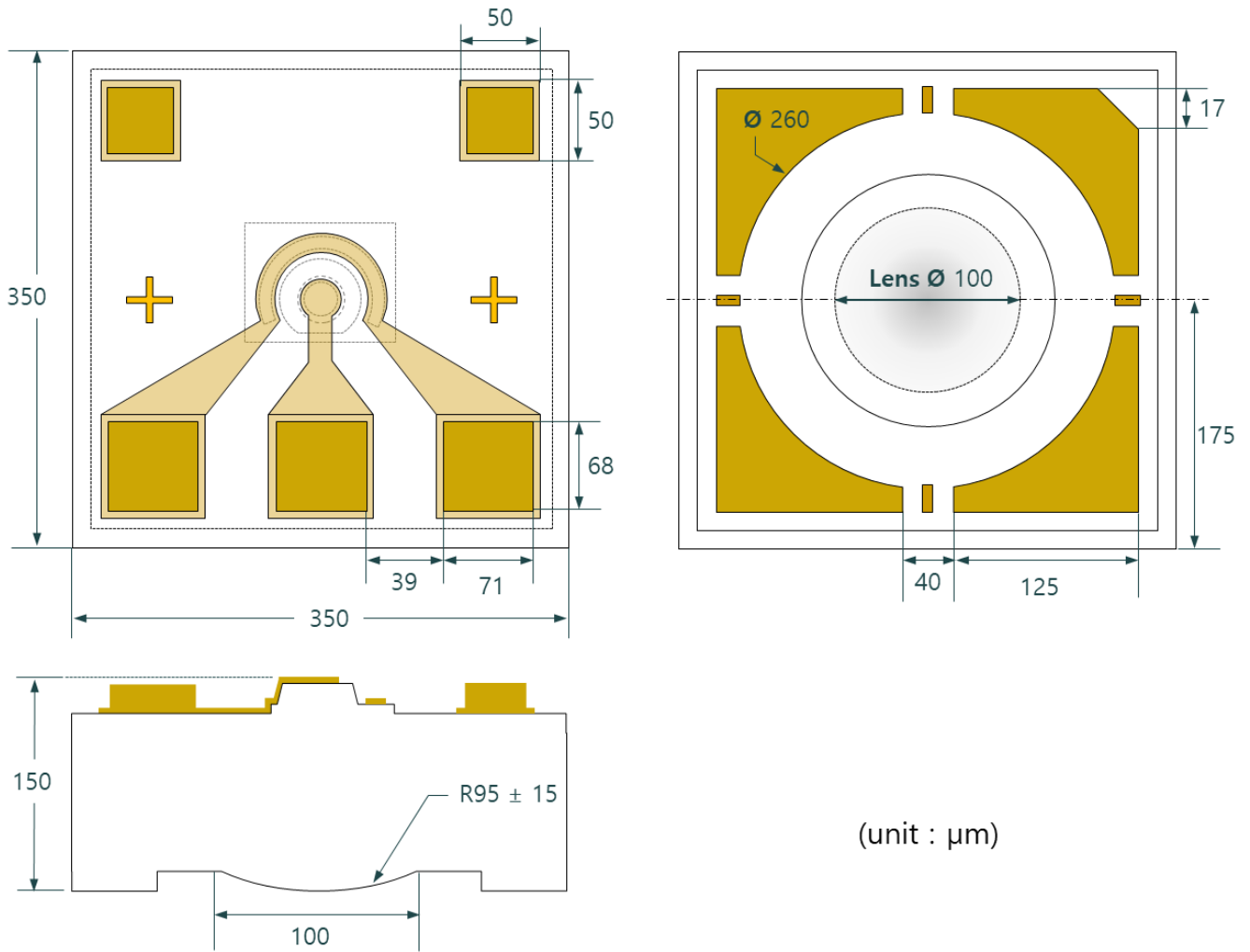
Electro-Optical Characteristics

Parameters	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Operating wavelength range	λ	-	1100	-	1640	nm
Responsivity*	R	1310nm, $V_R=2.5V$	0.7	0.8	-	A/W
Dark current	I_D	$V_R=5V$	-	1	10	nA
OE Bandwidth	BW	-3dB electrical	18	22	-	GHz
Total capacitance	C	f=1MHz, $V_R=2.5V$	-	0.08	0.09	pF

* depend on optical coupling efficiency

Dimensions

Parameters	Symbol	Size	Unit
Chip size	Sc	350 x 350	μm^2
Bonding pad size	Sp	68 x 71	μm^2
PD active diameter	D	20	μm
Lens ROC	R	95 ± 15	μm
Chip thickness	T	150 ± 15	μm



Precaution to use

The CPL2520S is sensitive to electrostatic discharge (ESD) and should be handled with appropriate caution. Please use standard ESD protective equipment when handling this product.

Ordering information

CPL2520S

Specifications described here are subject to change without notice

Tel: +82-62-602-8100
www.wooriro.com
support@wooriro.com